



DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV _{DSS}	Rds(on)	I _D T _A = +25°C
30V	1.2Ω @ V _{GS} = 4.5V	0.68A
307	1.5Ω @ V _{GS} = 2.5V	0.61A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Features and Benefits

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)

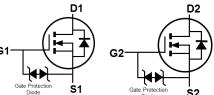




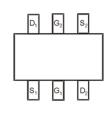


SOT563

Top View







Top View Pin Out

Ordering Information (Note 4)

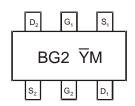
Part Number	Package	Packing		
Part Number	Fackage	Qty.	Carrier	
DMN32D0LV-7	SOT563	3000	Tape & Reel	
DMN32D0LV-13	SOT563	10000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



 $\begin{array}{l} \underline{BG2} = Product\ Type\ Marking\ Code\\ \overline{Y}M = Date\ Code\ Marking\\ \overline{Y} = Year\ (ex:\ J=2022)\\ M = Month\ (ex:\ 9=September) \end{array}$

Date Code Key

Year	2014		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	В		J	K	L	М	N	0	Р	R	S	Т
Manth												
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain Source Voltage		V _{DSS}	30	V
Gate-Source Voltage	Continuous	Vgss	±10	V
Drain Current (Note 5)	Continuous	ID	0.68	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	480	mW
Thermal Resistance, Junction to Ambient (Note 5)	RθJA	261	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



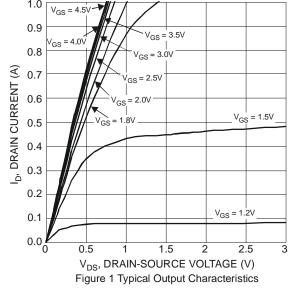
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

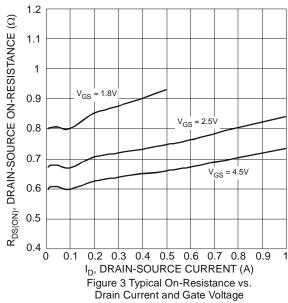
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V$, $I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1.0	μA	$V_{DS} = 30V$, $V_{GS} = 0V$
Gate-Body Leakage	Igss	_	_	10	μA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	Vgs(TH)	0.6	_	1.2	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		_	_	1.2		$V_{GS} = 4.0V, I_{D} = 100mA$
Static Drain-Source On-Resistance	RDS(ON)			1.5	Ω	$V_{GS} = 2.5V, I_{D} = 20mA$
		_	_	2.2		$V_{GS} = 1.8V, I_D = 20mA$
Source-Drain Diode Forward Voltage	V _{SD}	_	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	44.8	1	pF	
Output Capacitance	Coss	_	4.6	-	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.5	_	pF	1 - 1.01/11/12
Total Gate Charge	Qg	_	0.62	_	nC	15)/)/ 45)/
Gate-Source Charge	Qgs	_	0.12	1	nC	$V_{GS} = 4.5V, V_{DS} = 15V$ -In = 350mA
Gate-Drain Charge	Qgd	_	0.24	_	nC	TID = 330ITIA
Turn-On Delay Time	t _{D(ON)}	_	3.41	_	ns	
Turn-On Rise Time	t _R	_	2.45	_	ns	$V_{DD} = 20V$, $R_L = 250\Omega$
Turn-Off Delay Time	tD(OFF)		19.0	_	ns	$V_{GEN} = 4.5V$, $R_{GEN} = 6\Omega$
Turn-Off Fall Time	t _F		7.86	_	ns	

Notes:

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.







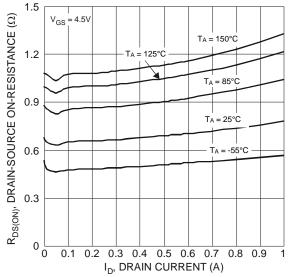
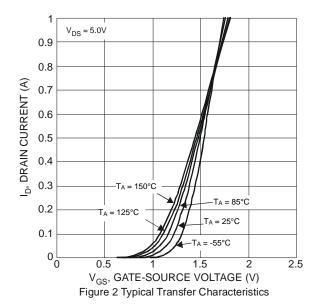
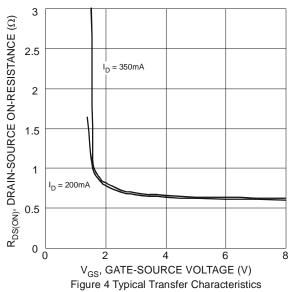


Figure 5 Typical On-Resistance vs. Drain Current and Temperature





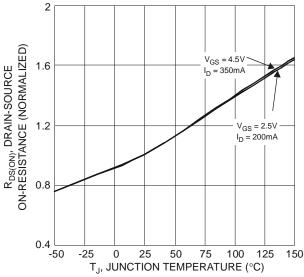
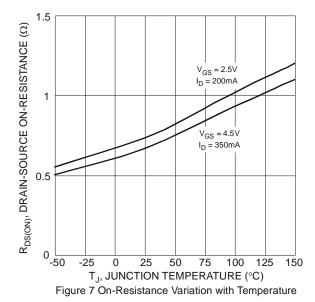
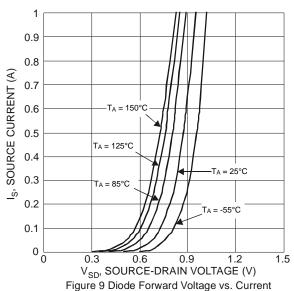
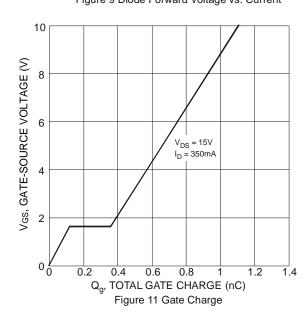


Figure 6 On-Resistance Variation with Temperature









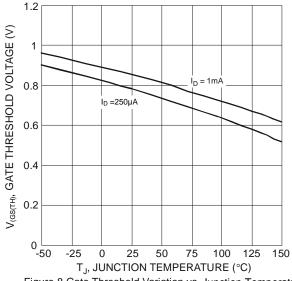
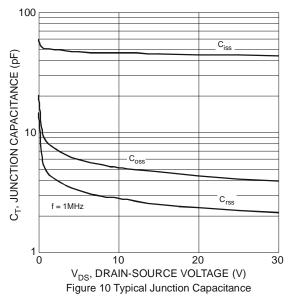
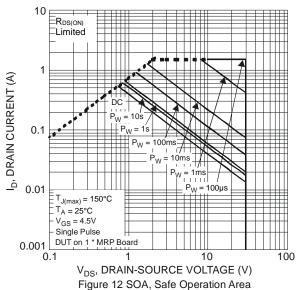
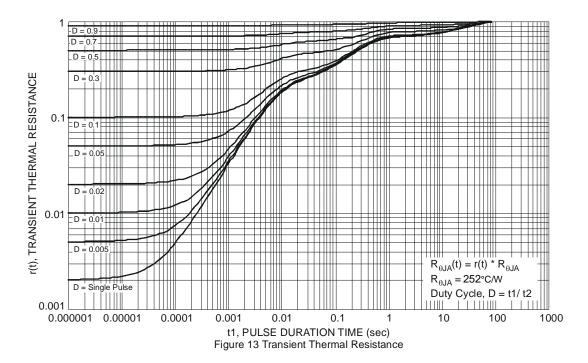


Figure 8 Gate Threshold Variation vs. Junction Temperature







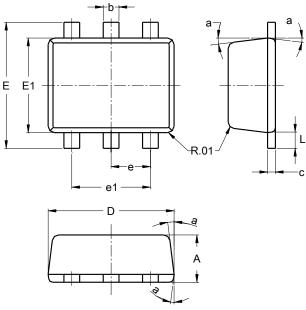




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563

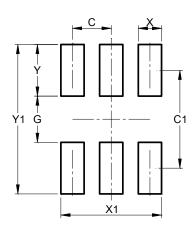


SOT563						
Dim	Min	Max	Тур			
Α	0.55	0.60				
b	0.15	0.30	0.20			
С	0.10	0.18	0.11			
D	1.50	1.70	1.60			
E	1.55	1.70	1.60			
E1	1.10	1.25	1.20			
е			0.50			
e1	0.90	1.10	1.00			
L	0.10	0.30	0.20			
а	8°	9°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
С	0.500
C1	1.270
G	0.600
Х	0.300
X1	1.300
Υ	0.670
Y1	1.940



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